

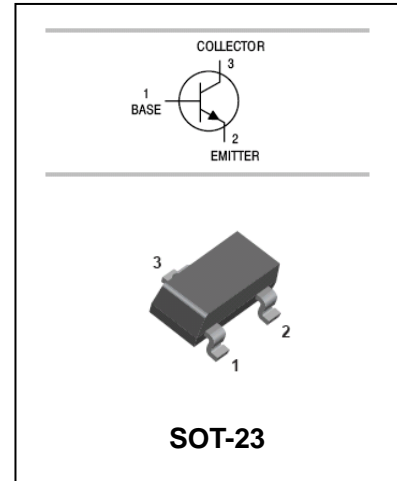


Silicon Epitaxial Planar Transistor

2SC2715

FEATURES

- High power gain
- Recommended for FM IF, OSC stage and AM CONV. IF stage



APPLICATIONS

- High Frequency Amplifier Applications

ORDERING INFORMATION

Type No.	Marking	Package Code
2SC2715	RR1/RO1/R1	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	35	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4	V
I _C	Collector Current -Continuous	50	mA
I _B	Base current	10	mA
P _C	Collector Dissipation	150	mW
T _j , T _{stg}	Junction and Storage Temperature	-55 to +125	°C



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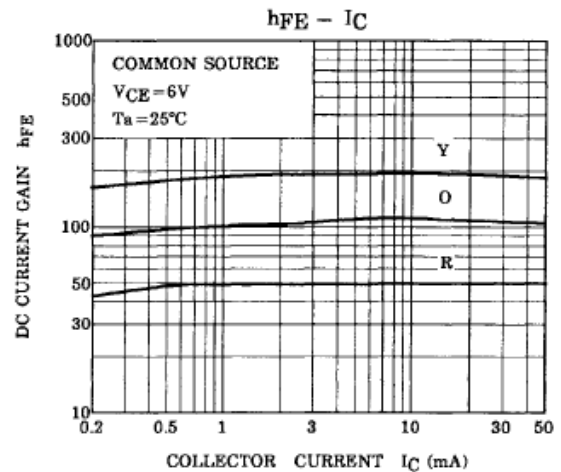
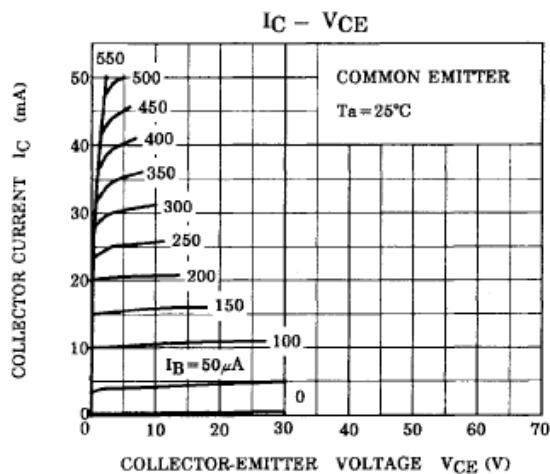
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=12V, I_C=2mA$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.4	V
Base-emitter voltage	V_{BE}	$I_C=10mA, I_B=1mA$			1	V
Transition frequency	f_T	$V_{CE}=10V, I_C=1mA$	100		400	MHz
Collector-base output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		2.0	3.2	pF
Collector-base time constant	$C_{c.rbb}$	$V_{CE}=10V, I_E=-1mA, f=30MHz$			50	ps
Power Gain	G_{pe}	$V_{CC}=6V, I_E=-1mA, f=10.7MHz$	27	30	33	dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	40-80	70-140	120-240
Marking	RR1	RO1	RY1

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



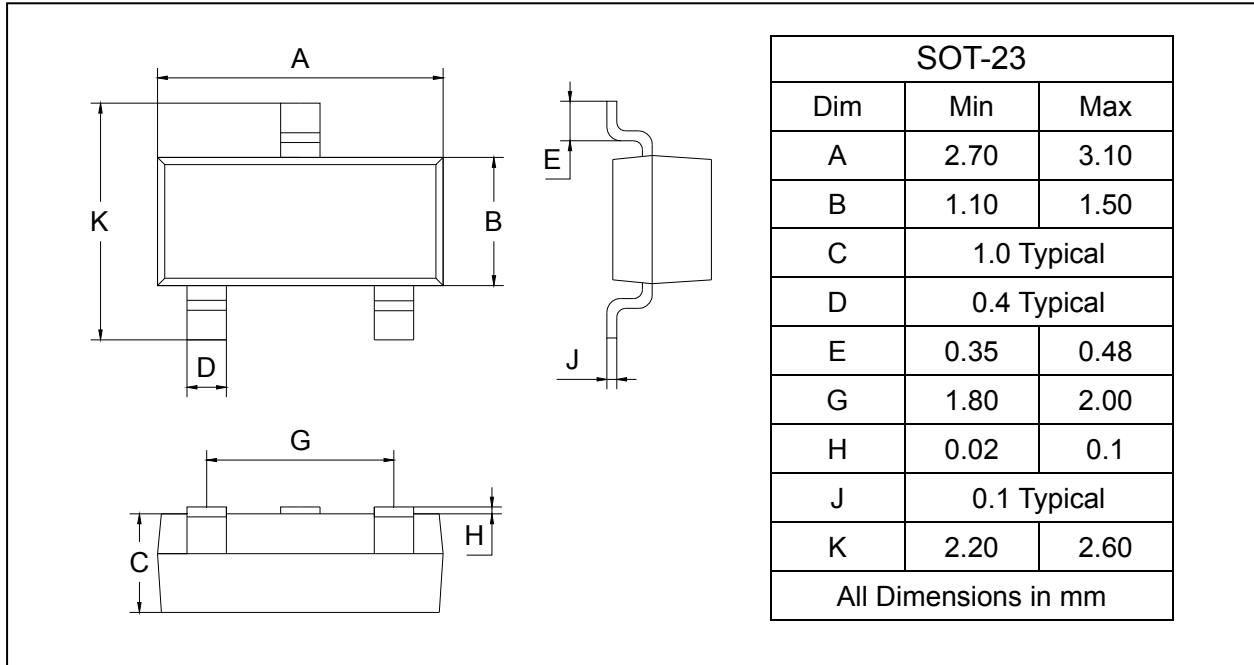
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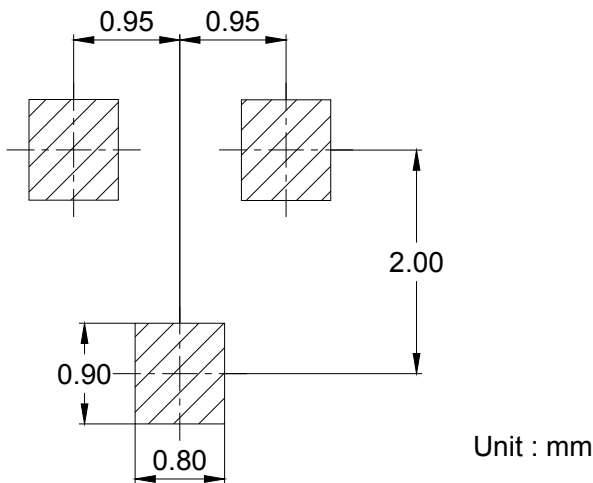
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SC2715	SOT-23	3000/Tape&Reel